

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A semiconductor laser array comprising:
 - a GaAs substrate;
 - a first laser element portion provided on said substrate to release laser light of a first wavelength; and
 - a second laser element portion provided on said substrate to release laser light of a second wavelength different from said first wavelength in a direction substantially parallel to the laser light of the first wavelength,
 - said first laser element portion including a first cladding layer, an active layer formed by epitaxially growing a first semiconductor material on said first cladding layer, a second cladding layer formed on said active layer and a current-blocking layer to confine an electrical current injected into said first laser element portion,
 - said second laser element portion including a first cladding layer, an active layer formed by epitaxially growing a second semiconductor material on said first cladding layer, a second cladding layer formed on said active layer and a current-blocking layer to confine an electrical current injected into said second laser element portion, and
 - said current-blocking layer of said first laser element portion and said current-blocking layer of said second laser element portion are made of same semiconductor material.
2. (Reinstated-formerly claims #2) The semiconductor laser array according to claim 1 wherein said first and second cladding layers of said first laser element portions are made of AlGaAs, and said first and second cladding layers of said second laser element portions are made of $\text{InGa}_{1-x}\text{Al}_x\text{P}$ ($0 < x \leq 1$).

3. (Reinstated-formerly claims #3) The semiconductor laser array according to claim 1 wherein group-V species included in said second cladding layer of said first laser element portion is not identical to group-V species

included in said current-blocking layer of said first laser element portion, and group-V species included in said second cladding layer of said second laser element portion is not identical to group-V species included in said current-blocking layer of said second laser element portion.

4. (Reinstated-formerly claims #4) The semiconductor laser array according to claim 3 wherein said second cladding layers of said first and second laser element portions are made of same semiconductor material.

5. (Reinstated-formerly claims #5) The semiconductor laser array according to claim 4 wherein said second cladding layers of said first and second laser element portions are made of InGaAlP.

6. (Reinstated-formerly claims #6) The semiconductor laser array according to claim 4 wherein said second cladding layer of said second laser element portion is configured as a ridge stripe extending along laser cavity lengthwise directions and both sides of said ridge stripe is buried by said current-blocking layer.

7. (Reinstated-formerly claims #7) The semiconductor laser array according to claim 4 wherein said first wavelength ranges about 780 nm as its center, and said second wavelength ranges about one of 635 nm, 650 nm and 685 nm as its center.

8. (Reinstated-formerly claims #8) The semiconductor laser array according to claim 4 wherein said active layer of said first laser element portion includes an AlGaAs layer, and said active layer of said second laser element portion includes an $\text{In}(\text{Ga}_{1-y}\text{Al}_y)\text{P}$ ($0 \leq y \leq 0.2$) layer.

9. (Reinstated-formerly claims #9) The semiconductor laser array according to claim 8 wherein said active layer of said first laser element portion has a bulk structure and said active layer of said second laser element portion has a multiple-quantum well structure.

10. (Reinstated-formerly claims #10) A semiconductor laser array comprising:

a GaAs substrate;

a first laser element portion provided on said substrate to release laser light of a first wavelength; and

a second laser element portion provided on said substrate to release laser light of a second wavelength different from said first wavelength in a direction substantially parallel to the laser light of the first wavelength,

said first laser element portion including a first cladding layer made of InGaAlP, an active layer formed on said first cladding layer, a second cladding layer formed on said active layer and made of InGaAlP, a stripe-shaped intermediate layer formed on said second cladding layer and made of a semiconductor material having a smaller band gap than said second cladding layer, and top layer formed to cover said second cladding layer and said intermediate layer and made of a semiconductor material having a smaller band gap than said intermediate layer.

said second laser element portion including a first cladding layer made of InGaAlP, an active layer formed on said first cladding layer, a second cladding layer formed on said active layer and made of InGaAlP, a stripe-shaped intermediate layer formed on said second cladding layer and made of a semiconductor material having a smaller band gap than said second cladding layer, and top layer formed to cover said second cladding layer and said intermediate layer and made of a semiconductor material having a smaller band gap than said intermediate layer.

11. (Reinstated-formerly claims #11) The semiconductor laser array according to claim 10 wherein said second cladding layer of said second laser

element portion is configured as a ridge stripe extending along laser cavity lengthwise directions and both sides of said ridge stripe is buried by said top layer.

12. (Reinstated-formerly claims #12) The semiconductor laser array according to claim 10 wherein said first wavelength ranges about 780 nm as its center, and said second wavelength ranges about one of 635 nm, 650 nm and 685 nm as its center.

13. (Reinstated-formerly claims #13) The semiconductor laser array according to claim 10 wherein said active layer of said first laser element portion includes an AlGaAs layer, and said active layer of said second laser element portion includes an $\text{In}(\text{Ga}_{1-y}\text{Al}_y)\text{P}$ ($0 \leq y \leq 0.2$) layer.